
Design Example Report

Title	<i>High Efficiency ($\geq 85\%$), High Power Factor (>0.9) 15 W LED Driver (Non-Dimming) Using LinkSwitchTM-PH LNK417EG with Active Ripple Filter</i>
Specification	90 VAC – 265 VAC Input; 30 V, 500 mA Output
Application	LED Driver
Author	Applications Engineering Department
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Summary and Features

- $<30\%$ $I_{\text{RIPPLE PK-PK}}$; achieved using an active ripple filter circuit
- Highly energy efficient
 - $\geq 85\%$ at 115 VAC and 230 VAC input
- Low cost, low component count and small printed circuit board footprint solution
 - No current sensing required
 - Frequency jitter for smaller, lower cost EMI filter components
- Integrated protection and reliability features
 - Output open-circuit / output short-circuit protection with auto-recovery
 - Line input overvoltage shutdown extends voltage withstand during line faults.
 - Auto-recovering thermal shutdown with large hysteresis protects both components and printed circuit board
 - No damage during brown-in or brown-out conditions
- Meets IEC 61000-4-5 ring wave, IEC 61000-3-2 Class C harmonics and EN55015 B conducted EMI
- Clean monotonic start-up – no output blinking
- Fast start-up (<100 ms) – no perceptible delay

PATENT INFORMATION

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Important Note: Although this board is designed to satisfy safety isolation requirements, the engineering prototype has not been agency approved. Therefore, all testing should be performed using an isolation transformer to provide the AC input to the prototype board.



1 Introduction

This document describes an isolated, power factor corrected, very high efficiency LED driver (non-dimmable) designed to drive an LED string of 30 V at a current of 500 mA (both nominal) from an input voltage range of 90 to 265 VAC. The design employs an active ripple filter to achieve less than 30% output ripple. A reference board DER-284 was used with active ripple filter daughter board.

The LED driver uses a LNK417EG device from the LinkSwitch-PH family of ICs. This integrated controller and 725 V MOSFET dramatically reduces the complexity and component count of the solution.

This document contains the LED driver specification, schematic, bill of material, and transformer documentation and typical performance characteristics.



2 Populated Circuit Board

2.1 Reference Board DER-284 and Active Ripple Filter Board

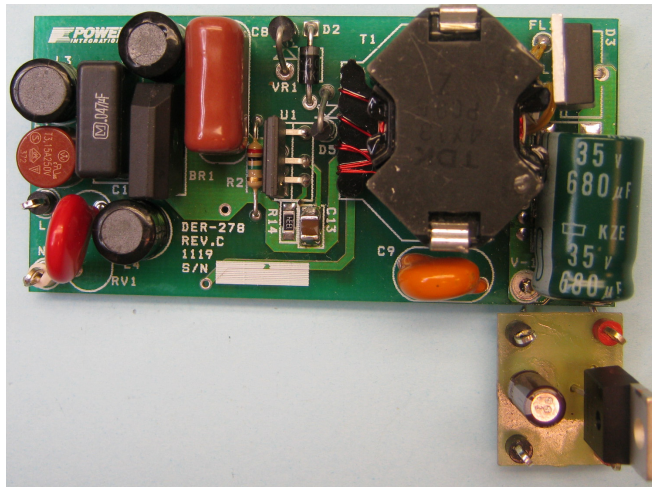


Figure 1 – Reference Board DER-284 and Active Ripple Filter Board. (Top View)

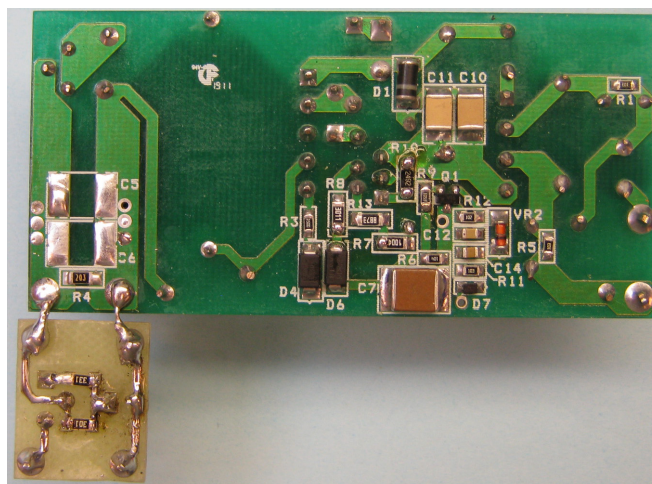


Figure 2 – Reference Board DER-284 and Active Ripple Filter Board. (Bottom View)

3 Power Supply Specification

The table below represents the minimum acceptable performance of the design. Actual performance is listed in the results section.

Description	Symbol	Min	Typ	Max	Units	Comment
Input						
Voltage	V_{IN}	90	115/230	265	VAC	2 Wire – no P.E.
Frequency	f_{LINE}	47	50/60	64	Hz	
Output						
Output Voltage	V_{OUT}	27	30	33	V	Percentage of the Average Output Current
Output Current	I_{OUT}		0.50		A	
Current Ripple PK-PK			30		%	
Total Output Power						
Continuous Output Power	P_{OUT}		15		W	
Efficiency						
Full Load	$\eta_{(115)}$	85				Measured at P_{OUT} , 25 °C, 115 VAC
	$\eta_{(230)}$	85			%	Measured at P_{OUT} , 25 °C, 230 VAC
Environmental						
Conducted EMI		Meets CISPR 15B / EN55015B				IEC 61000-4-5, 200 A
Safety		Designed to meet IEC950 / UL1950 Class II				
Ring Wave (100 kHz)						
Differential Mode (L1-L2)			2.5		kV	
Common mode (L1/L2-PE)						
Power Factor		0.9				Measured at $V_{OUT(TYP)}$, $I_{OUT(TYP)}$ and 115/230 VAC
Harmonic Currents		EN 61000-3-2 Class C				Class C Limits at $P_{IN} \leq 25$ W are Equal to Class D Limits
Ambient Temperature ^a	T_{AMB}		40		°C	Free convection, sea level

Notes:

^a Maximum ambient temperature specification may be increased by adding a small heat sink to the LinkSwitch-PH device.



4 Schematic

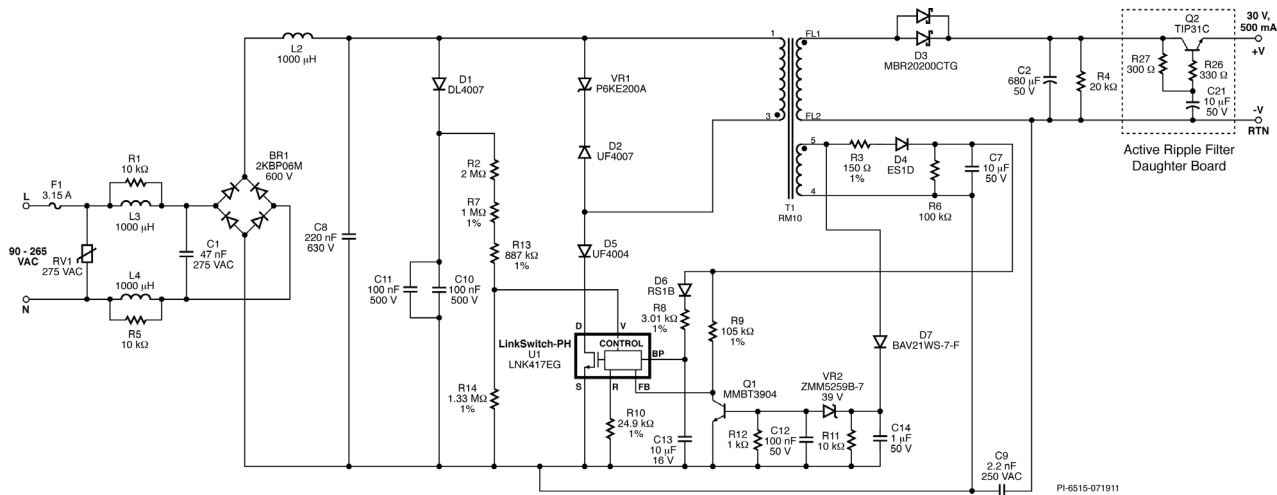


Figure 3 – Schematic of RD-284 and Active Ripple Filter.

Note: The original ceramic output capacitors were changed to a single 680 µF electrolytic capacitor



5 PCB Layout

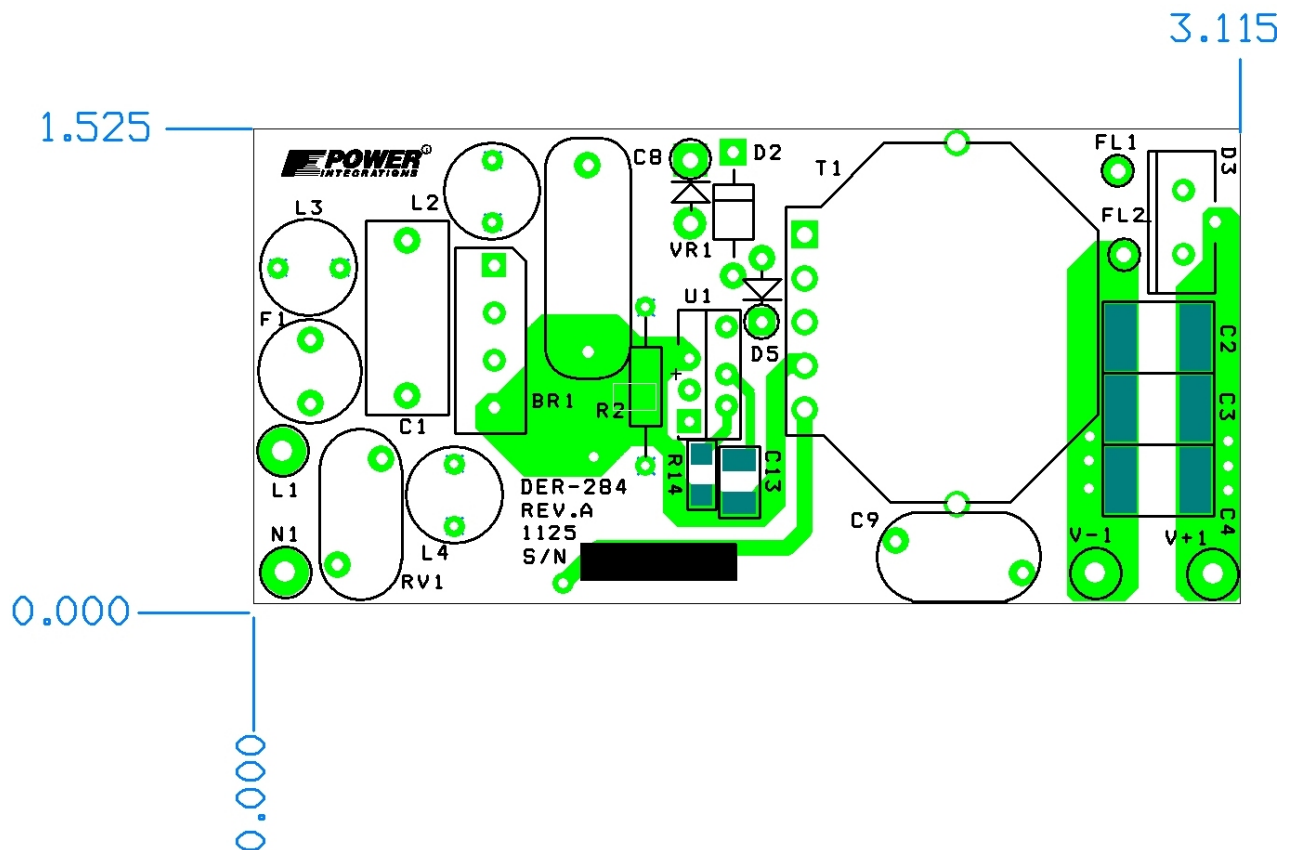


Figure 4 – PCB Layout DER-284 Board, Top.

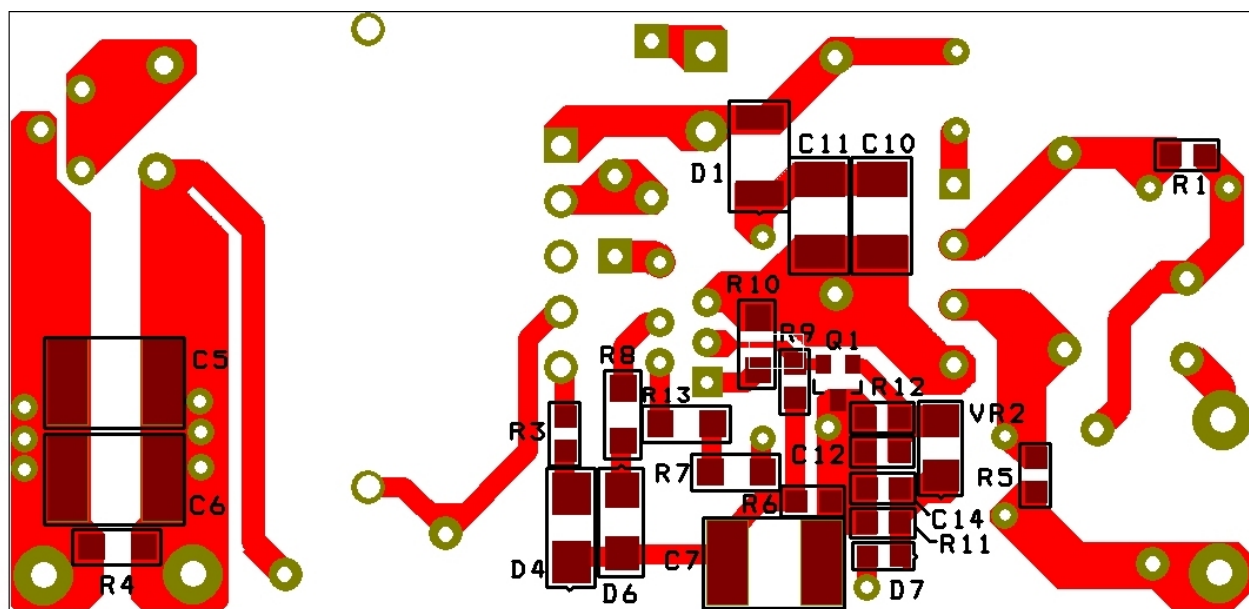


Figure 5 – PCB Layout DER-284 Board, Bottom.

Note: The original ceramic output capacitors were changed to a single 680 μ F electrolytic capacitor

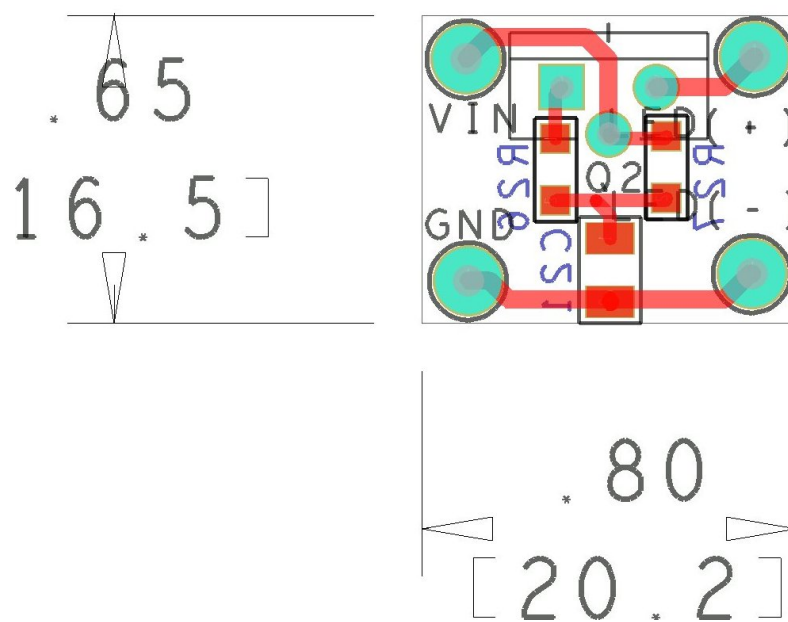


Figure 6 – PCB Layout Active Ripple Filter.



6 Description

The LinkSwitch-PH device is a controller and integrated 725 V MOSFET intended for use in LED driver applications. The LinkSwitch-PH is configured for use in a single-stage continuous conduction mode flyback topology and provides a primary side regulated constant current output while maintaining high power factor from the AC input.

6.1 Input Filtering

Fuse F1 protects the input and BR1 rectifies the AC line voltage. Inductor L2-L4, C1, R1, and R5 form the EMI filter and together with C9 (Y1 safety) capacitor allow the design to meet EN55015B conducted EMI limits. Capacitor C8 provides a low impedance path for the primary switching current, a low value of capacitance is necessary to maintain a power factor of greater than 0.9.

6.2 LinkSwitch-PH Primary

Diode D1 and high-voltage SMD ceramic capacitors C11 and C10 detect the peak AC line voltage. This voltage is converted to a current into the VOLTAGE MONITOR (V) pin via R2, R7 and R13. This current is also used by the device to set the input over/undervoltage protection thresholds. The V pin current and the FEEDBACK (FB) pin current are used by the IC to control the average output LED current. Non-dimming designs require 24.9 k Ω resistor on the REFERENCE (R) pin (R10) and 3.9 M Ω on the V pin (R2+R7+R13). Resistor R10 also sets the internal references to select the line undervoltage threshold. Resistor R14 is added to further improve line regulation, providing a constant output current over the specified input voltage range.

Diode D2 and VR1 clamp the drain voltage to below the BV_{DSS} rating (725 V) of the internal power MOSFET in U1. Diode D5 is necessary to prevent reverse current from flowing through the LinkSwitch-PH device (the result of the minimal input capacitance).

6.3 Bias Supply and Output Overvoltage Sensing

Diode D4, D6, C7, R3, R6 and R8 form the primary bias supply. This supplies the IC operating current to the BYPASS (BP) pin through D6 and R8 during normal operation. Resistor R3 provides filtering to improve output regulation while R6 acts as a minimum load.

Capacitor C13 provides decoupling for the LinkSwitch-PH. During start-up C13 is charged to ~6 V from an internal high-voltage current source tied to the device DRAIN (D) pin. Once charged the energy stored in C13 is used to run the device until the output and bias winding voltage rise and current can be supplied via R8.

A disconnected load / overvoltage shutdown function is provided by D7, C14, R11, VR2, C12, R12 and Q1. A second voltage from the bias-winding is used to reduce the delay that is introduced by the large value of C7 (compared to C14). Should the output LED load be disconnected, the output voltage (and therefore the bias winding voltage across C14) will rise. Once this exceeds the voltage rating of VR2 plus the V_{BE} of Q1, Q1 is



biased on which pulls down the FB pin. Once the current into the FB pin of U1 falls below $I_{FB(AR)}$ the device enters auto-restart, thereby limiting the output voltage. Resistor R11, C12 provide filtering and R12 set the Zener current at the point Q1 turns on.

6.4 Output Feedback

A current from the primary bias-winding, proportional to the output voltage, is fed into the FB pin through R9. This information together with the line input voltage and the drain current are used to maintain a constant output current.

6.5 Output Rectification and Filtering

Diode D3 rectifies the secondary winding while electrolytic capacitor C2 smoothes the output. A 20 A, 200 V Schottky diode was selected for high efficiency. Optional resistor R4 provides a minimum load to ensure the LED current falls when the AC is removed (for bench testing).

6.6 Active Ripple Filtering

Resistor R27 and C21 filter the ripple voltage. The corner frequency of network R27/C21 is set below the line frequency to reduce the 120 Hz line frequency ripple present at the output. Resistor R26 limits the base current flowing into the transistor during output short circuit condition.

The benefit of eliminating large ripple does not come without penalty. Transistor Q1 dissipates heat as it blocks the AC line ripple from the input. The heat dissipation is determined by the amount of ripple that is going to be rejected.

6.7 Considerations for higher efficiency

The following changes were made to a standard RD-195 to achieve higher efficiency.

- Larger LinkSwitch-PH device (LNK417EG vs. LNK416EG).
- 20 A vs. 4 A Schottky output diode.
- Larger RM10 core size vs. RM8 to allow lower winding current density (and lower winding losses).
- High value of electrolytic capacitor (680 μ F) to minimize the power dissipation across the Q2 of the active ripple filter circuit (and achieve <30% ripple current).



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7 Bill of Materials

Item	Qty	Ref Des	Description	Mfg Part Number	Mfg
1	1	BR1	600 V, 2 A, Bridge Rectifier, Glass Passivated	2KBP06M-E4/51	Vishay
2	1	C1	47 nF, 275 VAC, Film, X2	ECQU2A473ML	Panasonic
3	5	C2	680 μ F, 35 V		United Chemi-con
4	1	C7	10 μ F, 50 V, Ceramic, X7R, 2220	C5750X7R1H106M	TDK
5	1	C8	220 nF, 630 V, Film	ECQ-E6224KF	Panasonic
6	1	C9	2.2 nF, Ceramic, Y1	440LD22-R	Vishay
7	2	C10, C11	100 nF, 500 V, Ceramic, X7R, 1812	VJ1812Y104KXEAT	Vishay
8	1	C12	100 nF, 50 V, Ceramic, X7R, 0805	ECJ-2YB1H104K	Panasonic
9	1	C13	10 μ F, 16 V, Ceramic, X5R, 1210	C1210C106K4PACTU	Kemet
10	1	C14	1 μ F, 50 V, Ceramic, X7R, 0805	08055D105KAT2A	AVX
11	1	C21	10 μ F, 16 V, e-cap		United Chemi-con
12	1	D1	1000 V, 1 A, Rectifier, Glass Passivated, DO-213AA (MELF)	DL4007-13-F	Diodes, Inc.
13	1	D2	1000 V, 1 A, Ultrafast Recovery, 75 ns, DO-41	UF4007-E3	Vishay
14	1	D3	200 V, 10 A, Dual Schottky, TO-220AB	MBR20200CTG	ON Semi
15	1	D4	200 V, 1 A, Ultrafast Recovery, 25 ns, DO-214AC	ES1D	Vishay
16	1	D5	400 V, 1 A, Ultrafast Recovery, 50 ns, DO-41	UF4004-E3	Vishay
17	1	D6	100 V, 1 A, Fast Recovery, 150 ns, SMA	RS1B-13-F	Diodes, Inc.
18	1	D7	250 V, 0.2 A, Fast Switching, 50 ns, SOD-323	BAV21WS-7-F	Diodes, Inc.
19	1	F1	3.15 A, 250 V, Slow, TR5	37213150411	Wickman
20	3	L1,L2,L3	1000 μ H, 0.3 A	RLB0914-102KL	Bourns
21	1	Q1	NPN, Small Signal BJT, 40 V, 0.2 A, SOT-23	MMBT3904LT1G	On Semi
22	1	Q2	NPN, Power BJT, 30 V, 3 A, TIP31C	TIP31C	On Semi
23	3	R1, R5, R11	10 k Ω , 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ103V	Panasonic
24	1	R2	2.0 M Ω , 5%, 1/4 W, Carbon Film	CFR-25JB-2M0	Yageo
25	1	R3	150 Ω , 1%, 1/8 W, Thick Film, 0805	ERJ-6ENF1500V	Panasonic
26	1	R4	20 k Ω , 5%, 1/4 W, Thick Film, 1206	ERJ-8GEYJ203V	Panasonic
27	1	R6	100 k Ω , 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ104V	Panasonic
28	1	R7	1.00 M Ω , 1%, 1/4 W, Thick Film, 1206	ERJ-8ENF1004V	Panasonic
29	1	R8	3.01 k Ω , 1%, 1/4 W, Thick Film, 1206	ERJ-8ENF3011V	Panasonic
30	1	R9	105 k Ω , 1%, 1/8 W, Thick Film, 0805	ERJ-6ENF1053V	Panasonic
31	1	R10	24.9 k Ω , 1%, 1/8 W, Thick Film, 0805	ERJ-6ENF2492V	Panasonic
32	1	R12	1 k Ω , 5%, 1/8 W, Thick Film, 0805	ERJ-6GEYJ102V	Panasonic
33	1	R13	887 k Ω , 1%, 1/4 W, Thick Film, 1206	ERJ-8ENF8873V	Panasonic
34	1	R14	1.33 M Ω , 1%, 1/4 W, Thick Film, 1206	MCR18EZH1334	Rohm
35	1	R26	330 Ω , 5%, 1/4 W, Thick Film, 1206	ERJ-8GEYJ331V	Panasonic
36	1	R27	300 Ω , 5%, 1/4 W, Thick Film, 1206	ERJ-8GEYJ301V	Panasonic
37	1	RV1	275 V, 80J, 10 mm, RADIAL	ERZ-V10D431	Panasonic
38	1	T1	Custom transformer, RM10, Vertical, 5 pins	P-1031	Pin Shine
39	1	U1	LinkSwitch, eSIP	LNK417EG	Power Integrations
40	1	VR1	200 V, 5 W, 5%, TVS, DO204AC (DO-15)	P6KE200ARLG	On Semi
41	1	VR2	39 V, 5%, 500 mW, DO-213AA (MELF)	ZMM5259B-7	Diodes, Inc.



8 Transformer Specification

8.1 Electrical Diagram

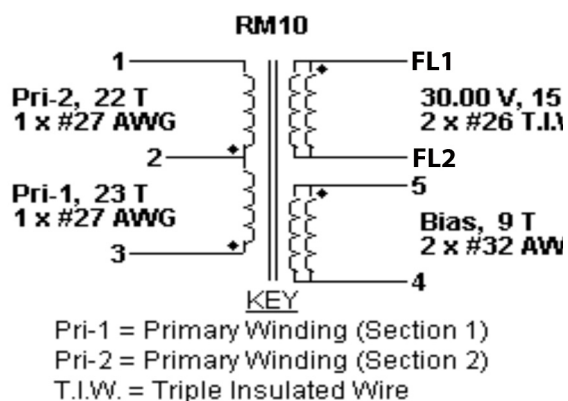


Figure 7 – Transformer Electrical Diagram.

8.2 Electrical Specifications

Electrical Strength	1 second, 60 Hz, from pins 1, 2, 3, 4, 5 to pins FL1, FL2.	3000 VAC
Primary Inductance	Measured at 1 V pk-pk, typical switching frequency, between pin 1 to pin 3, with all other windings open.	1.6 mH $\pm 10\%$
Resonant Frequency	Pins 1-FL1, all other windings open	750 kHz (Min.)
Primary Leakage Inductance	Measured between pin 1 to pin 3, with all other windings shorted.	40 μ H $\pm 10\%$

8.3 Materials

Item	Description
[1]	Core: PC95RM10Z-12 or Equivalent, gapped for ALG of 792 nH/t ²
[2]	Bobbin: Generic, 5 primary + 0 secondary
[3]	Barrier Tape: Polyester film [1 mil (25 μ m) base thickness], 10.00 mm wide
[4]	Separation Tape: Polyester film [1 mil (25 μ m) base thickness], 10.0 mm wide
[5]	Varnish
[6]	Magnet Wire: #27 AWG, Solderable Double Coated
[7]	Triple Insulated Wire: 26 AWG
[8]	Magnet Wire: #32 AWG, Solderable Double Coated
[9]	Clip: CLI/P-RM10/I



8.4 Transformer Build Diagram

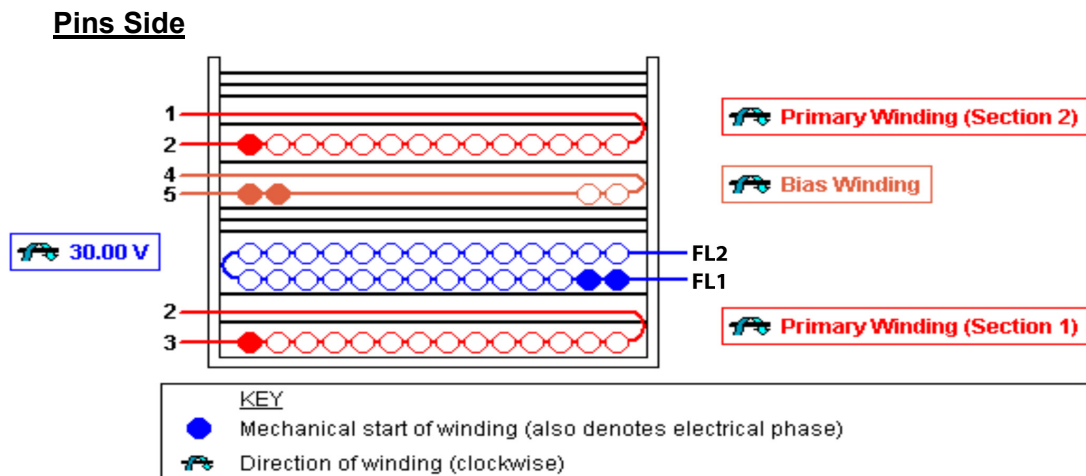


Figure 8 – Transformer Build Diagram.

8.5 Transformer Construction

Bobbin Preparation	Place the bobbin item [2] on the mandrel such that pin side on the left side. Winding direction is the clockwise direction.
Primary Winding 1	Start on pin 3 and wind 23 turns (x1 filar) of item [6] in 1 layer(s) from left to right. Add 1 layer of tape, item [4], in between each primary winding layer. On the final layer, spread the winding evenly across entire bobbin. Finish this winding on pin 2.
Insulation	Add 1 layer of tape, item [3], for insulation.
Secondary Winding	Start on pin FL1 and wind 15 turns (x2 filar) of item [7]. Spread the winding evenly across entire bobbin. Wind in same rotational direction as primary winding. Finish this winding on pin FL2.
Insulation	Add 3 layers of tape, item [3], for insulation.
Bias Winding	Start on pin 5 and wind 9 turns (x2 filar) of item [8]. Wind in same rotational direction as primary winding. Spread the winding evenly across entire bobbin. Finish this winding on pin(s) 4.
Insulation	Add 1 layer of tape, item [3], for insulation.
Primary Winding 2	Start on pin 2 and wind 22 turns (x1 filar) of item [6] in 1 layer(s) from left to right. Add 1 layer of tape, item [4], in between each primary winding layer. On the final layer, spread the winding evenly across entire bobbin. Finish this winding on pin 1.
Insulation	Add 3 layers of tape, item [3], for insulation.
Final Assembly	Assemble and secure core halves. Item [1] with Item [9]. Dip varnish uniformly in item [5]. Do not vacuum impregnate.

9 Transformer Design Spreadsheet

ACDC_LinkSwitch-PH_011111; Rev.1.2; Copyright Power Integrations 2011	INPUT	INFO	OUTPUT	UNIT	LinkSwitch-PH_011111: Flyback Transformer Design Spreadsheet
ENTER APPLICATION VARIABLES					
Dimming required	NO		NO		Select 'YES' option if dimming is required. Otherwise select 'NO'.
VACMIN			90	V	Minimum AC Input Voltage
VACMAX			265	V	Maximum AC input voltage
fL			50	Hz	AC Mains Frequency
VO	30.00			V	Typical output voltage of LED string at full load
VO_MAX			33.00	V	Maximum expected LED string Voltage.
VO_MIN			27.00	V	Minimum expected LED string Voltage.
V_OVP			36.30	V	Over-voltage protection setpoint
IO	0.50				Typical full load LED current
PO			15.0	W	!!! For Universal Input reduce Continuous Output Power PO_CONT below 12W (or use larger LinkSwitch-PH)
n	0.90		0.9		Estimated efficiency of operation
VB	17		17	V	Bias Voltage
ENTER LinkSwitch-PH VARIABLES					
LinkSwitch-PH	LNK417			Universal	115 Doubled/230V
Chosen Device		LNK417	Power Out	12W	5.5W
Current Limit Mode	RED		RED		Select "RED" for reduced Current Limit mode or "FULL" for Full current limit mode
ILIMITMIN			1.42	A	Minimum current limit
ILIMITMAX			1.66	A	Maximum current limit
fS			66000	Hz	Switching Frequency
fSmin			62000	Hz	Minimum Switching Frequency
fSmax			70000	Hz	Maximum Switching Frequency
IV			38.7	uA	V pin current
RV			3.909	M-ohms	Upper V pin resistor
RV2			1.402	M-ohms	Lower V pin resistor
IFB			126.3	uA	FB pin current (85 uA < IFB < 210 uA)
RFB1			110.8	k-ohms	FB pin resistor
VDS			10	V	LinkSwitch-PH on-state Drain to Source Voltage
VD	0.50			V	Output Winding Diode Forward Voltage Drop (0.5 V for Schottky and 0.8 V for PN diode)
VDB	0.70			V	Bias Winding Diode Forward Voltage Drop
Key Design Parameters					
KP	0.78		0.78		Ripple to Peak Current Ratio (For PF > 0.9, 0.4 < KP < 0.9)
LP			1603	uH	Primary Inductance
VOR	91.50		91.5	V	Reflected Output Voltage.
Expected IO (average)			0.48	A	Expected Average Output Current
KP_VACMAX			1.02		Expected ripple current ratio at VACMAX
TON_MIN			2.28	us	Minimum on time at maximum AC input voltage
PCLAMP			0.12	W	Estimated dissipation in primary clamp
ENTER TRANSFORMER CORE/CONSTRUCTION VARIABLES					
Core Type	RM10		RM10		
Bobbin		RM10_BOBBIN		P/N:	CPV-RM10-1S-12PD
AE			0.966	cm^2	Core Effective Cross Sectional Area
LE			4.46	cm	Core Effective Path Length
AL			4050	nH/T^2	Ungapped Core Effective Inductance
BW	10.0		10	mm	Bobbin Physical Winding Width
M			0	mm	Safety Margin Width (Half the Primary to Secondary Creepage Distance)
L	2.00		2		Number of Primary Layers
NS	15		15		Number of Secondary Turns



DC INPUT VOLTAGE PARAMETERS					
V _{MIN}			127	V	Peak input voltage at V _{ACMIN}
V _{MAX}			375	V	Peak input voltage at V _{ACMAX}
CURRENT WAVEFORM SHAPE PARAMETERS					
D _{MAX}			0.44		Minimum duty cycle at peak of V _{ACMIN}
I _{AVG}			0.17	A	Average Primary Current
I _P			0.81	A	Peak Primary Current (calculated at minimum input voltage V _{ACMIN})
I _{RMS}			0.28	A	Primary RMS Current (calculated at minimum input voltage V _{ACMIN})
TRANSFORMER PRIMARY DESIGN PARAMETERS					
L _P			1603	uH	Primary Inductance
N _P			45		Primary Winding Number of Turns
N _B			9		Bias Winding Number of Turns
AL _G			792	nH/T ²	Gapped Core Effective Inductance
B _M			2986	Gauss	Maximum Flux Density at P _O , V _{MIN} (B _M <3100)
B _P			3613	Gauss	Peak Flux Density (B _P <3700)
B _{AC}			1164	Gauss	AC Flux Density for Core Loss Curves (0.5 X Peak to Peak)
μ _r			1488		Relative Permeability of Ungapped Core
L _G			0.12	mm	Gap Length (L _G > 0.1 mm)
B _{WE}			20	mm	Effective Bobbin Width
OD			0.44	mm	Maximum Primary Wire Diameter including insulation
INS			0.06	mm	Estimated Total Insulation Thickness (= 2 * film thickness)
DIA			0.38	mm	Bare conductor diameter
AWG			27	AWG	Primary Wire Gauge (Rounded to next smaller standard AWG value)
CM			203	Cmils	Bare conductor effective area in circular mils
CMA		Warning	724	Cmils/Amp	!!! DECREASE CMA (200 < CMA < 600) Decrease L(primary layers),increase NS,smaller Core
L _{P_TOL}			10		Tolerance of primary inductance
TRANSFORMER SECONDARY DESIGN PARAMETERS (SINGLE OUTPUT EQUIVALENT)					
Lumped parameters					
I _{SP}			2.43	A	Peak Secondary Current
I _{SRMS}			0.90	A	Secondary RMS Current
I _{IRIPPLE}			0.75	A	Output Capacitor RMS Ripple Current
C _{MS}			180	Cmils	Secondary Bare Conductor minimum circular mils
AWG _S			27	AWG	Secondary Wire Gauge (Rounded up to next larger standard AWG value)
DIA _S			0.36	mm	Secondary Minimum Bare Conductor Diameter
OD _S			0.67	mm	Secondary Maximum Outside Diameter for Triple Insulated Wire
VOLTAGE STRESS PARAMETERS					
V _{DRAIN}			566	V	Estimated Maximum Drain Voltage assuming maximum LED string voltage (Includes Effect of Leakage Inductance)
P _{IVS}			161	V	Output Rectifier Maximum Peak Inverse Voltage (calculated at V _{OVP} , excludes leakage inductance spike)
P _{IVB}			93	V	Bias Rectifier Maximum Peak Inverse Voltage (calculated at V _{OVP} , excludes leakage inductance spike)
FINE TUNING (Enter measured values from prototype)					
V pin Resistor Fine Tuning					
R _{V1}			3.91	M-ohms	Upper V Pin Resistor Value
R _{V2}			1.40	M-ohms	Lower V Pin Resistor Value
V _{AC1}			115.0	V	Test Input Voltage Condition1
V _{AC2}			230.0	V	Test Input Voltage Condition2
I _{O_VAC1}			0.50	A	Measured Output Current at V _{AC1}
I _{O_VAC2}			0.50	A	Measured Output Current at V _{AC2}



RV1 (new)			3.91	M-ohms	New RV1
RV2 (new)			1.40	M-ohms	New RV2
V_OV			318.3	V	Typical AC input voltage at which OV shutdown will be triggered
V_UV			70.8	V	Typical AC input voltage beyond which power supply can startup
FB pin resistor Fine Tuning					
RFB1			111	k-ohms	Upper FB Pin Resistor Value
RFB2			1E+012	k-ohms	Lower FB Pin Resistor Value
VB1			15.3	V	Test Bias Voltage Condition1
VB2			18.7	V	Test Bias Voltage Condition2
IO1			0.50	A	Measured Output Current at Vb1
IO2			0.50	A	Measured Output Current at Vb2
RFB1 (new)			110.8	k-ohms	New RFB1
RFB2(new)			1.00E+12	k-ohms	New RFB2



10 Performance Data

All measurements performed at room temperature.

10.1 Efficiency vs. Line and Output (LED String) Voltage

10.1.1 30 V

Input		Input Measurement					Load Measurement			Calculation		
VAC (V _{RMS})	Freq (Hz)	V _{IN} (V _{RMS})	I _{IN} (mA _{RMS})	P _{IN} (W)	PF	%ATHD	V _{OUT} (V _{DC})	I _{OUT} (mA _{DC})	P _{OUT} (W)	P _{CAL} (W)	Efficiency (%)	Loss (W)
90	60	89.88	208.10	18.52600	0.99050	13.69	30.73	506.00	15.56	15.55	83.99	2.97
100	60	99.92	186.10	18.39200	0.98900	14.5	30.72	506.50	15.57	15.56	84.66	2.82
115	60	114.93	161.26	18.28400	0.98650	15.58	30.71	507.50	15.60	15.59	85.32	2.68
135	60	134.91	138.11	18.25800	0.97990	18.4	30.71	509.90	15.67	15.66	85.83	2.59
190	50	189.93	99.78	18.20400	0.96060	24.36	30.70	511.00	15.70	15.69	86.24	2.50
210	50	209.92	90.75	18.10300	0.95030	26.28	30.68	508.80	15.62	15.61	86.28	2.48
230	50	229.90	83.00	17.92700	0.93950	27.36	30.65	504.50	15.48	15.46	86.35	2.45
265	50	264.98	72.17	17.50500	0.91540	28.37	30.60	493.80	15.12	15.11	86.38	2.39

10.1.2 27 V

Input		Input Measurement					Load Measurement			Calculation		
VAC (V _{RMS})	Freq (Hz)	V _{IN} (V _{RMS})	I _{IN} (mA _{RMS})	P _{IN} (W)	PF	%ATHD	V _{OUT} (V _{DC})	I _{OUT} (mA _{DC})	P _{OUT} (W)	P _{CAL} (W)	Efficiency (%)	Loss (W)
90	60	89.89	186.64	16.59600	0.98910	14.45	27.50	504.70	13.89	13.88	83.69	2.71
100	60	99.93	167.56	16.53500	0.98750	15.32	27.50	506.40	13.94	13.93	84.31	2.60
115	60	114.94	145.76	16.49500	0.98460	16.45	27.51	508.40	13.99	13.99	84.81	2.51
135	60	134.91	125.29	16.51800	0.97710	19.3	27.51	511.90	14.09	14.08	85.30	2.43
190	50	189.93	90.71	16.48800	0.95700	24.79	27.51	513.00	14.12	14.11	85.64	2.37
210	50	209.93	82.51	16.38100	0.94580	26.51	27.49	510.10	14.04	14.02	85.71	2.34
230	50	229.90	75.52	16.20900	0.93350	27.41	27.47	505.10	13.89	13.88	85.69	2.32
265	50	264.99	65.96	15.82800	0.90560	28.22	27.42	494.00	13.56	13.55	85.67	2.27

10.1.3 33 V

Input		Input Measurement					Load Measurement			Calculation		
VAC (V _{RMS})	Freq (Hz)	V _{IN} (V _{RMS})	I _{IN} (mA _{RMS})	P _{IN} (W)	PF	%ATHD	V _{OUT} (V _{DC})	I _{OUT} (mA _{DC})	P _{OUT} (W)	P _{CAL} (W)	Efficiency (%)	Loss (W)
90	60	89.88	226.98	20.22700	0.99150	12.93	33.51	507.90	17.03	17.02	84.19	3.20
100	60	99.92	202.10	19.99700	0.99020	13.71	33.50	506.60	16.98	16.97	84.91	3.02
115	60	114.93	174.45	19.80800	0.98790	14.81	33.49	506.20	16.96	16.95	85.62	2.85
135	60	134.91	148.86	19.72300	0.98210	17.47	33.49	507.30	17.00	16.99	86.19	2.72
190	50	189.93	107.38	19.64200	0.96310	23.97	33.49	508.60	17.04	17.03	86.75	2.60
210	50	209.93	97.63	19.54100	0.95340	26.02	33.47	506.60	16.97	16.96	86.84	2.57
230	50	229.90	89.25	19.35800	0.94350	27.28	33.45	502.70	16.83	16.82	86.94	2.53
265	50	264.99	77.46	18.93100	0.92220	28.31	33.40	492.80	16.47	16.46	87.00	2.46



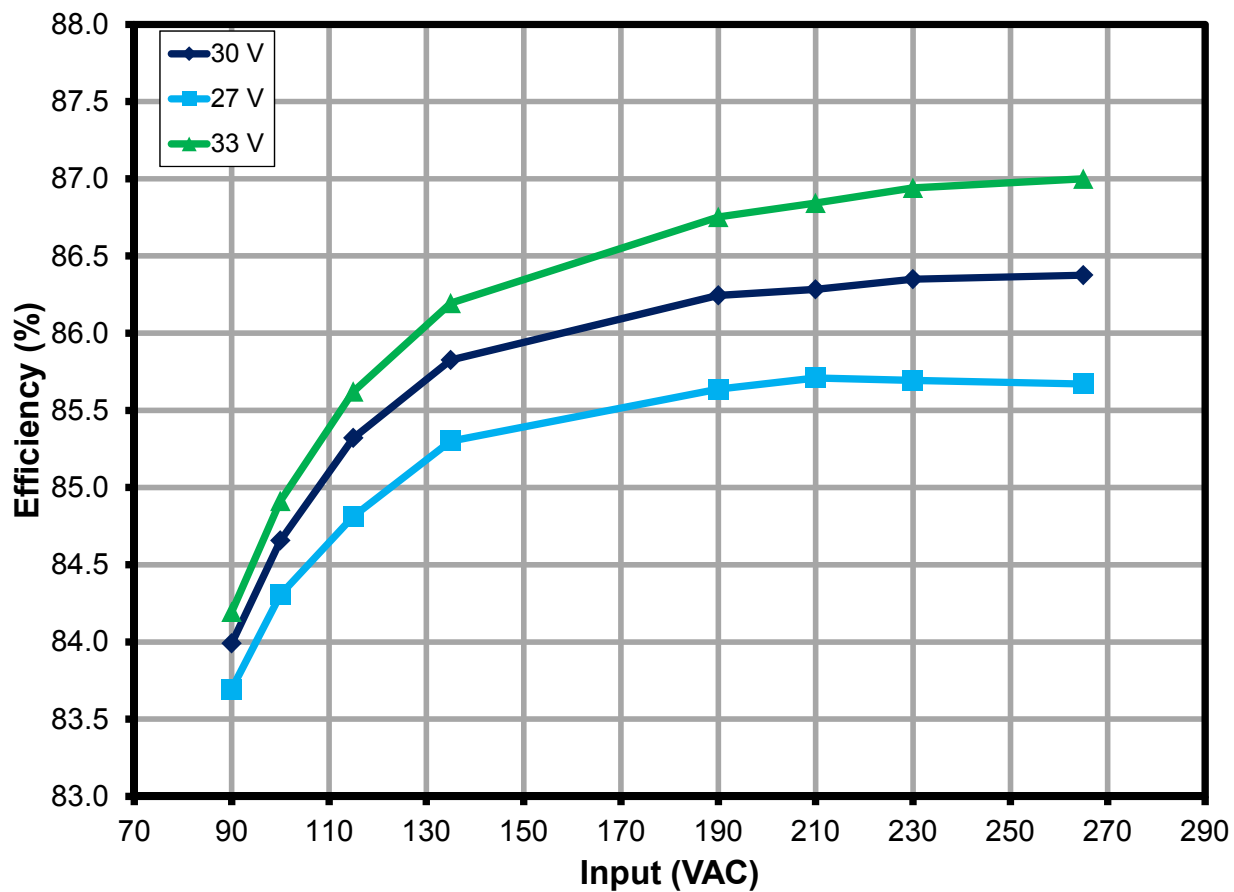


Figure 9 – Efficiency vs. Input Voltage, Room Temperature.



10.2 Regulation

10.2.1 Line Regulation

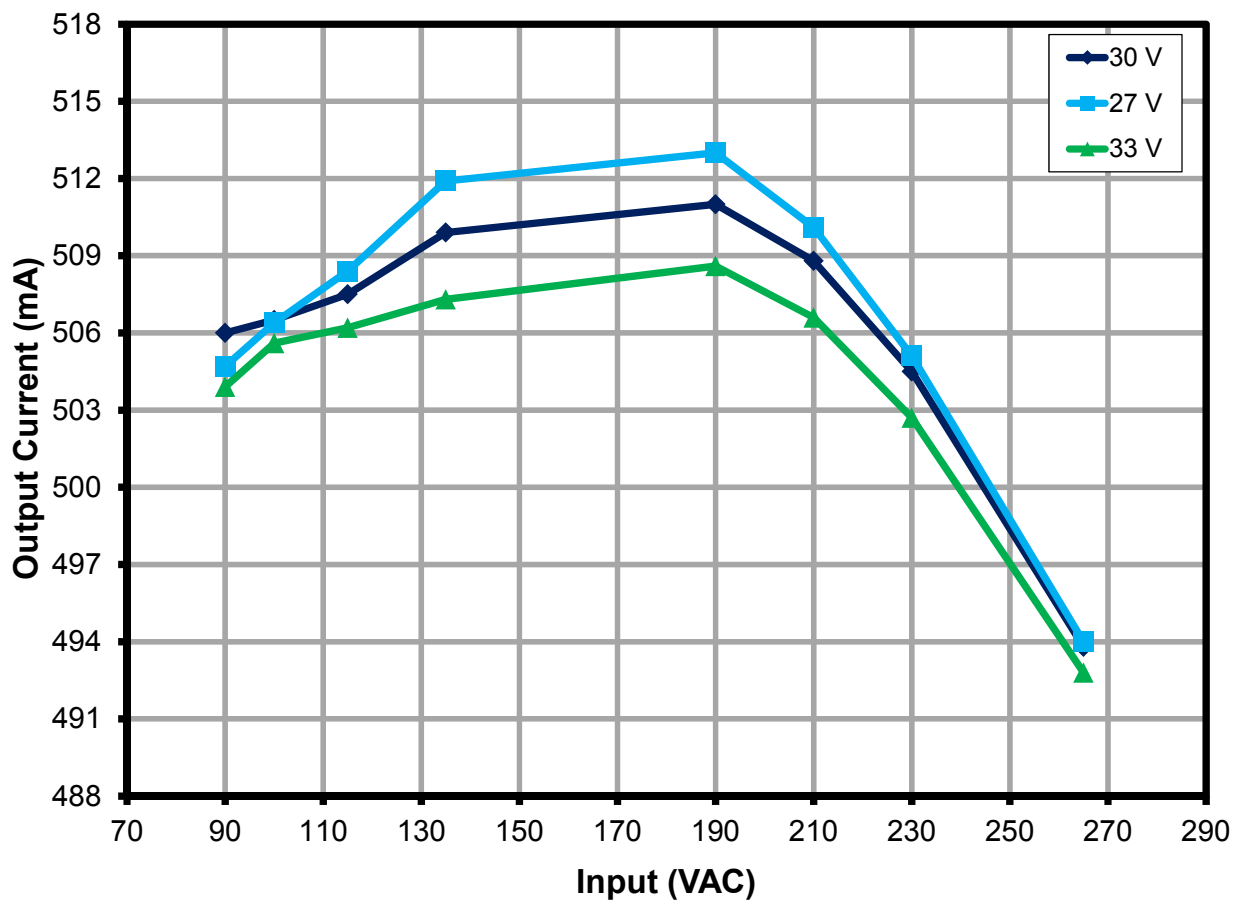


Figure 10 – Line Regulation, Room Temperature, Full Load.

10.3 Power Factor

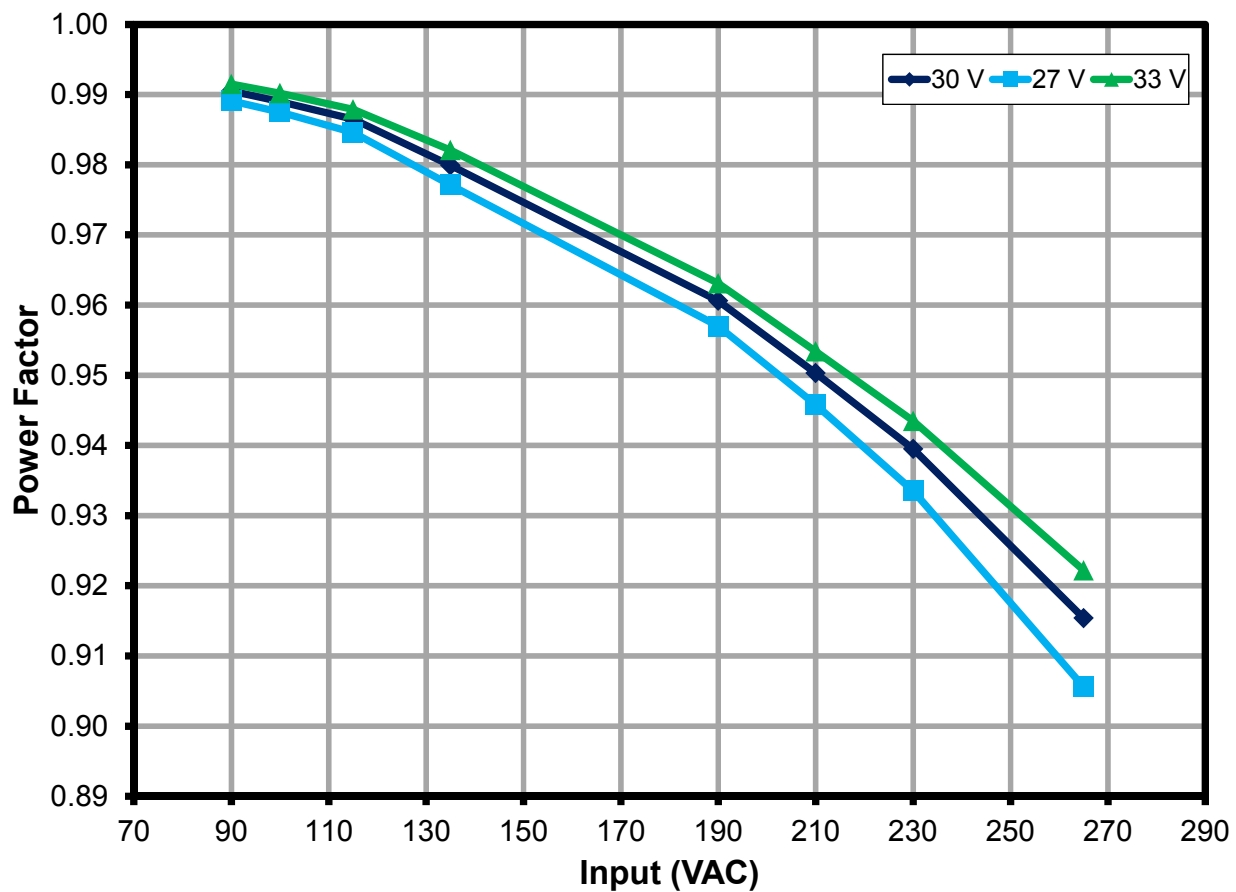


Figure 11 – Power Factor vs. Line, Room Temperature, Full Load.



11 Harmonic Data

The design passes Class C requirement.

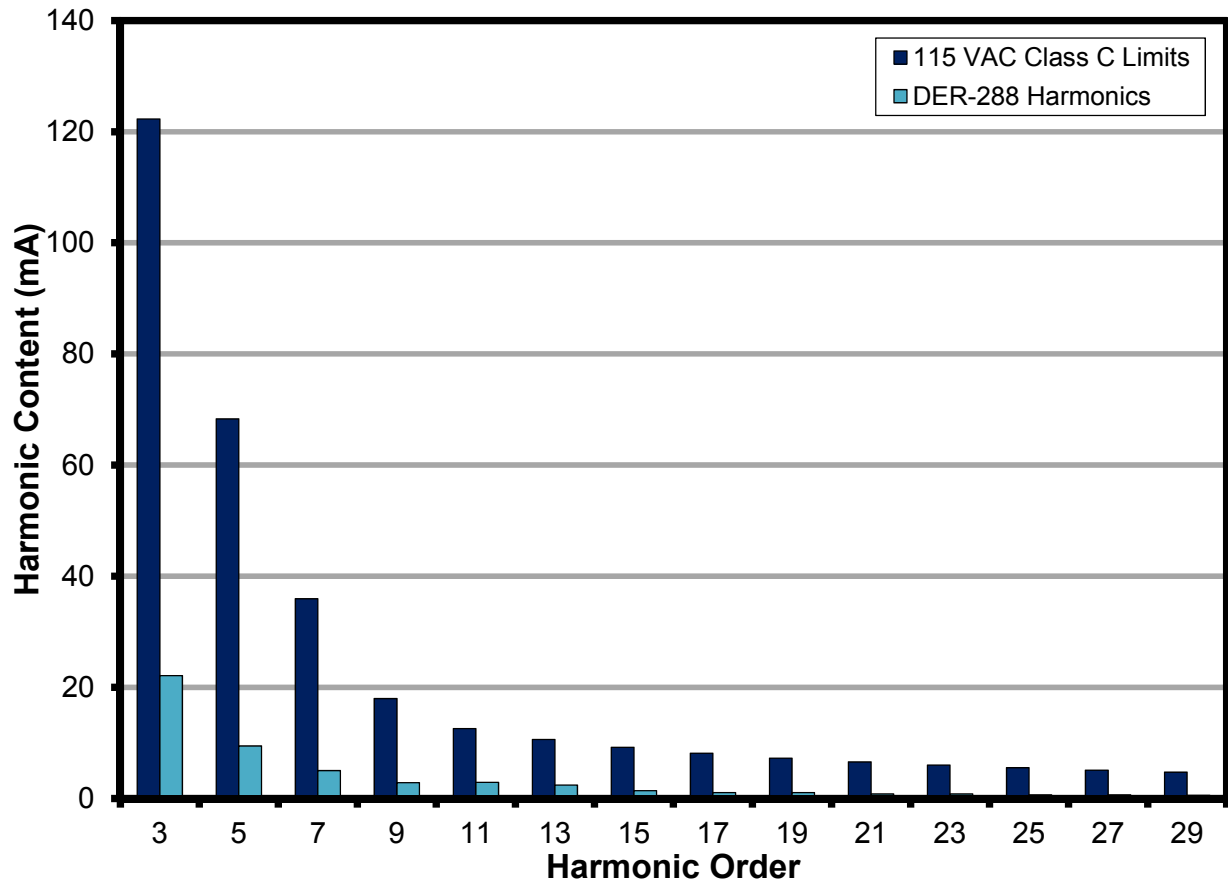


Figure 12 – 115 VAC Harmonic, Room Temperature, Full Load.

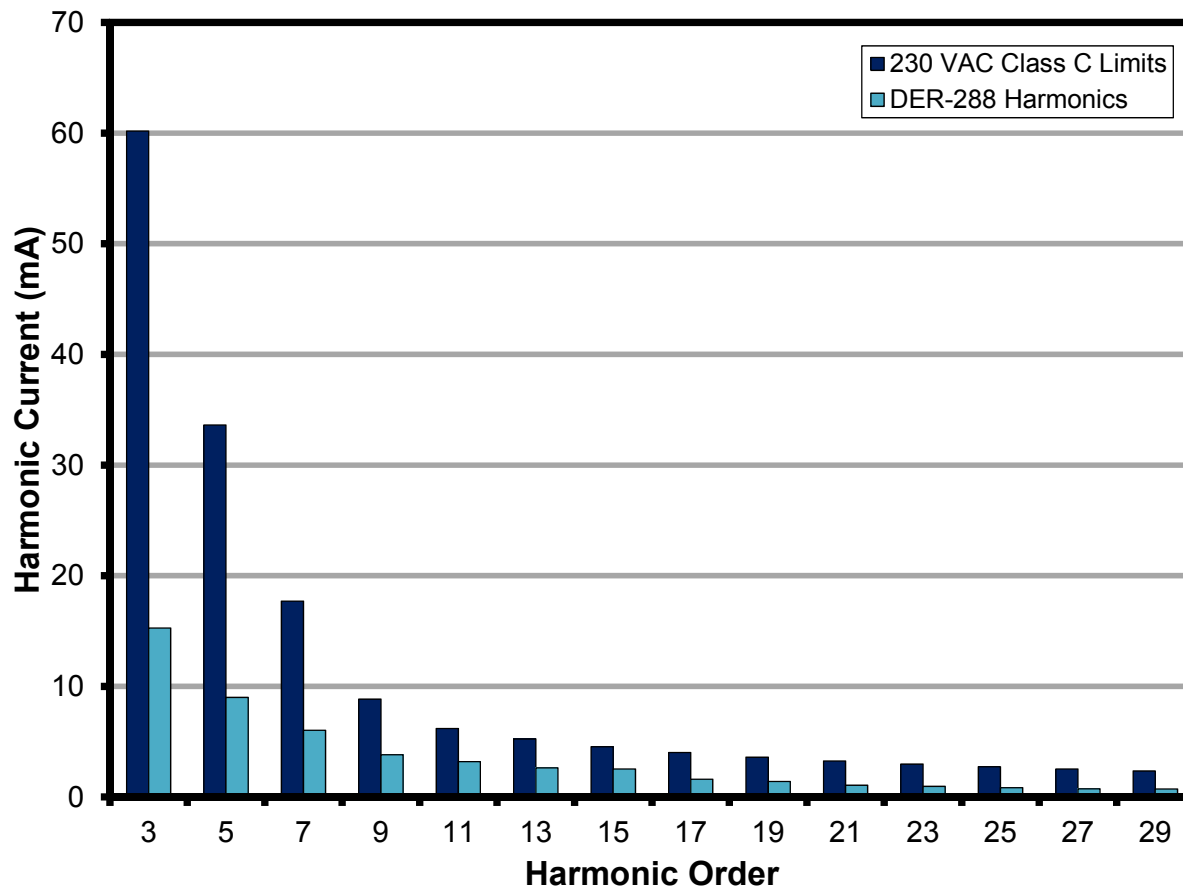


Figure 13 – 230 VAC Harmonic, Room Temperature, Full Load.

V _{IN} = 115 VAC		
THD (%)	Limit (%)	Margin (%)
16	33	16
V _{IN} = 230 VAC		
THD (%)	Limit (%)	Margin (%)
26	33	6



12 Waveforms

12.1 Input Line Voltage and Current

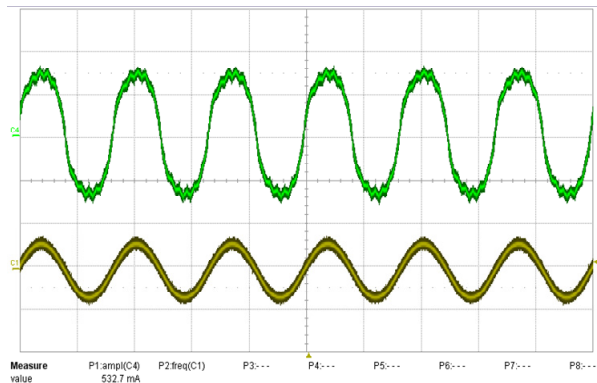


Figure 14 – 90 VAC, Full Load.
Upper: I_{IN} , 0.2 A / div.
Lower: V_{IN} , 200 V, 10 ms / div.

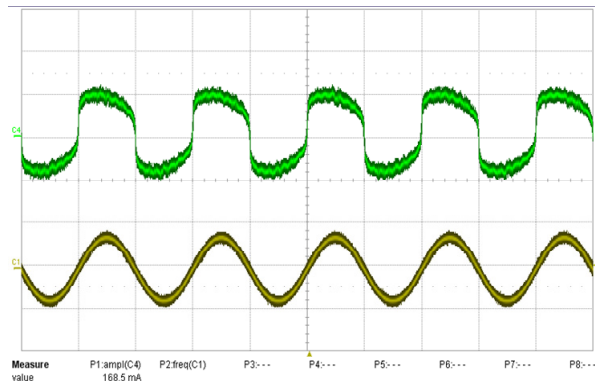


Figure 15 – 265 VAC, Full Load.
Upper: I_{IN} , 0.1 A / div.
Lower: V_{IN} , 500 V / div., 10 ms / div.

12.2 Drain Voltage and Current

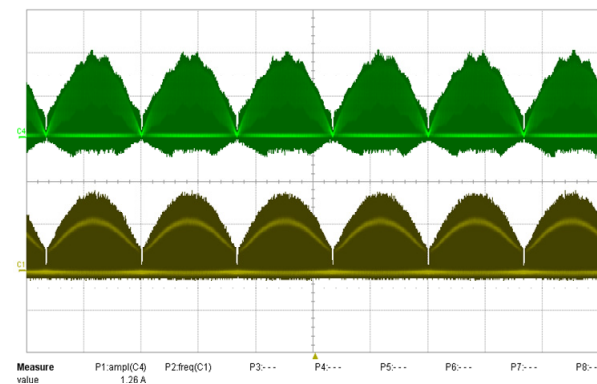


Figure 16 – 90 VAC, Full Load.
Upper: I_{DRAIN} , 0.5 A / div.
Lower: V_{DRAIN} , 200 V, 5 ms / div.

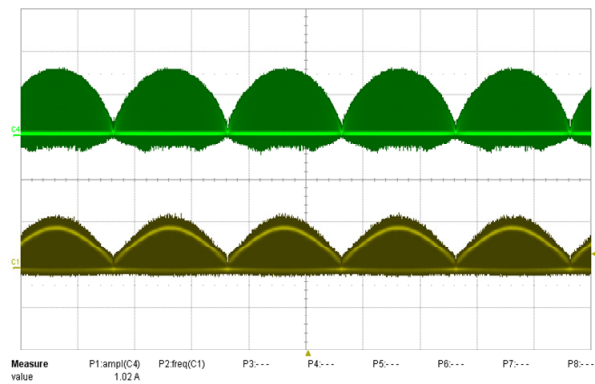


Figure 17 – 265 VAC, Full Load.
Upper: I_{DRAIN} , 0.5 A / div.
Lower: V_{DRAIN} , 500 V / div., 5 ms / div.

12.3 Output Voltage and Ripple Current

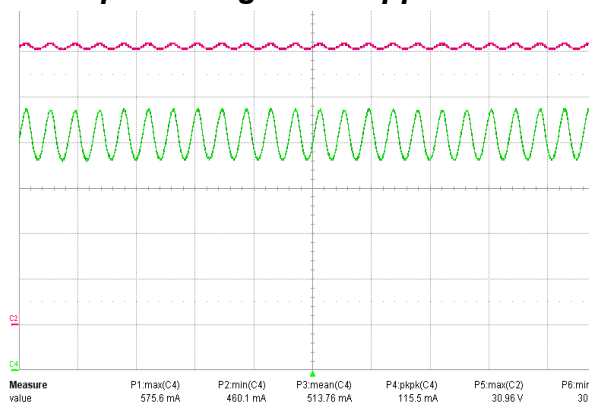


Figure 18 – 90 VAC, Full Load.

Upper: $I_{RIPPLE\ PK-PK}$, 115 mA
 Lower: V_{OUT} , 5 V, 5 ms / div

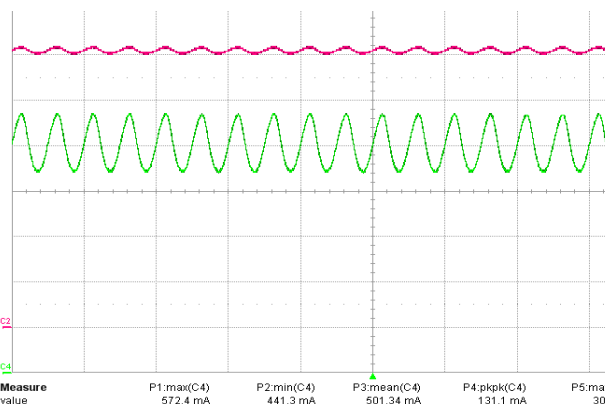
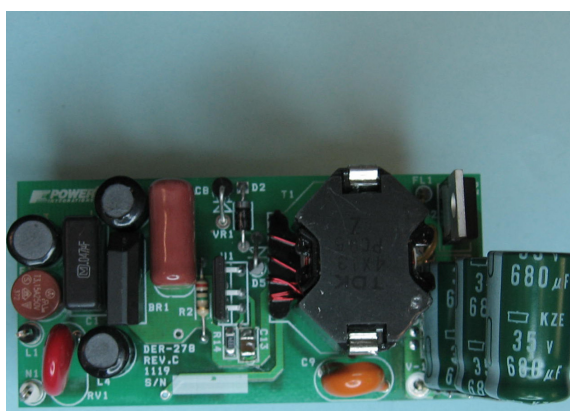
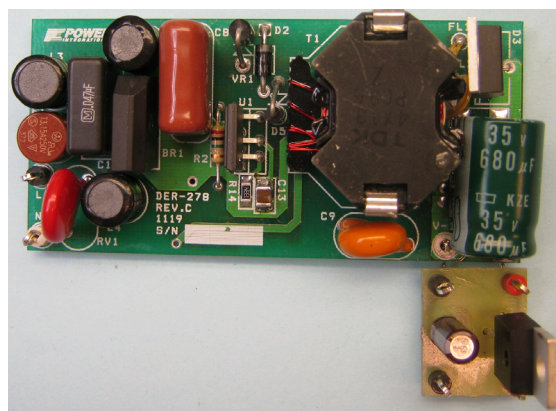


Figure 19 – 265 VAC, Full Load.

Upper: $I_{RIPPLE\ PK-PK}$, 131 mA
 Lower: V_{OUT} , 5 V, 5 ms / div.



The supply with an active ripple filter (right photo) used only one output capacitor as opposed to the a supply without an ARF would need 3X as much output capacitance to match the same 30% ripple.

12.4 Output Ripple vs. Efficiency

Since the Active Ripple Circuit is a dissipative circuit, the lower the output current ripple is set the lower the efficiency becomes.

The curves with higher output capacitor values show higher efficiency overall because the fundamental ripple is lower.

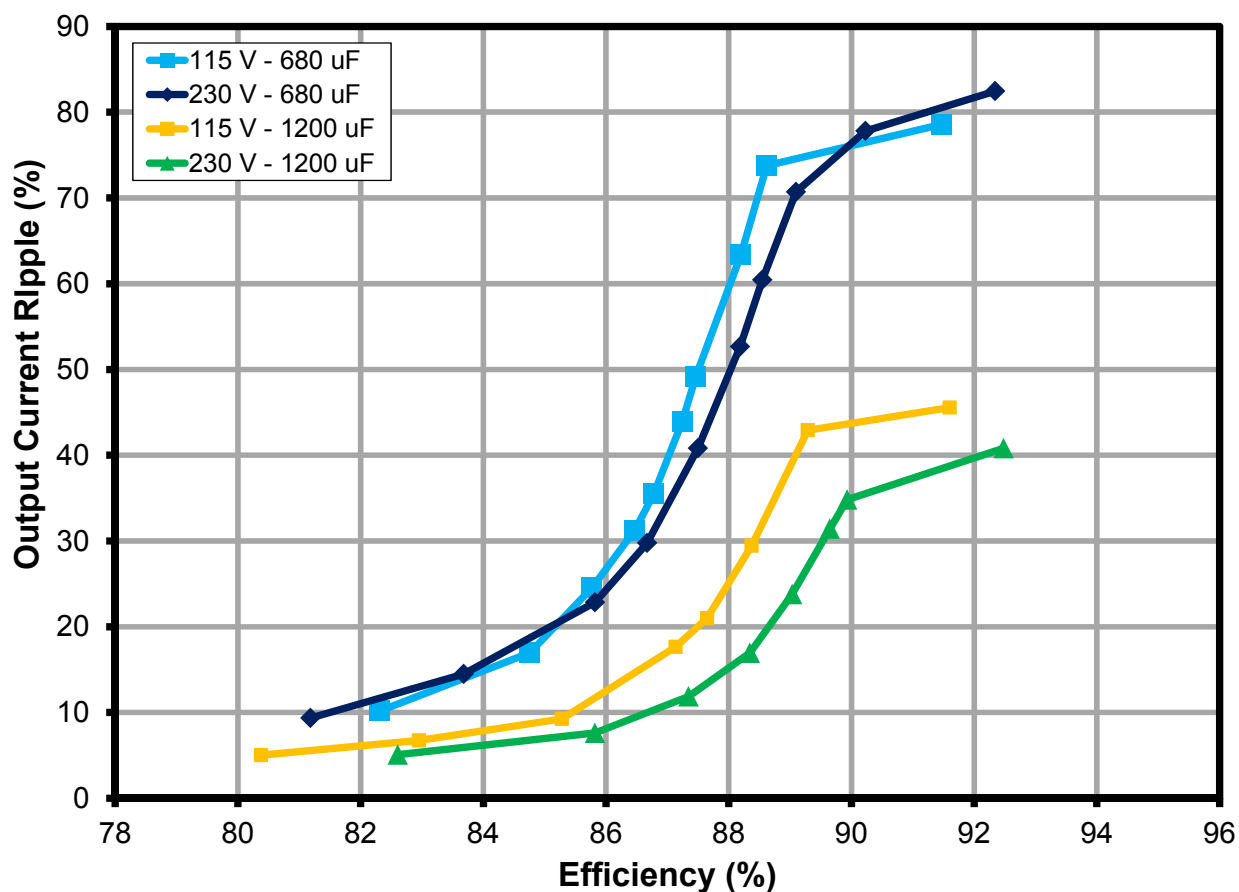


Figure 20 – Output Ripple vs. Efficiency.

12.5 Output Rectifier Voltage and Current

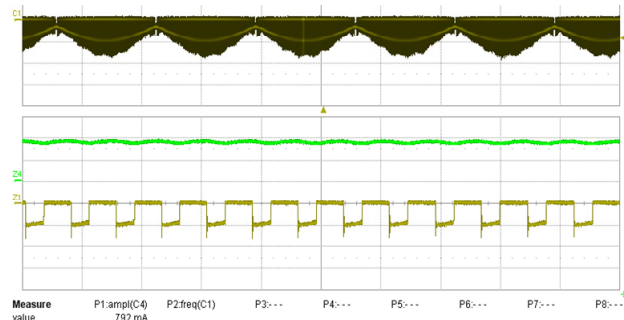


Figure 21 – 110 VAC, Full Load.
Upper: I_{RIPPLE} , 0.5 A / div.
Lower: V_{DIODE} , 100 V, 5 ms/200 μ s / div.

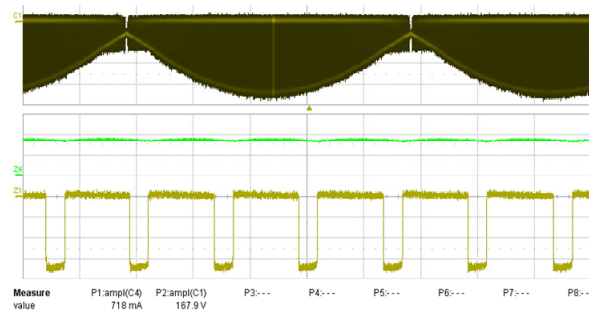


Figure 22 – 265 VAC, Full Load.
Upper: I_{RIPPLE} , 0.5 A / div.
Lower: V_{DIODE} , 100 V, 5 ms/200 μ s / div.

12.6 Output Current and Drain Voltage with Shorted Output

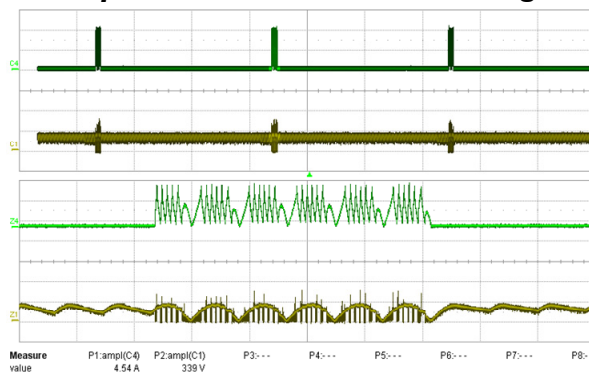


Figure 23 – 90 VAC, Full Load.
Upper: I_{OUT} , 2 A / div.
Lower: V_{DRAIN} , 200 V, 500 ms / div.

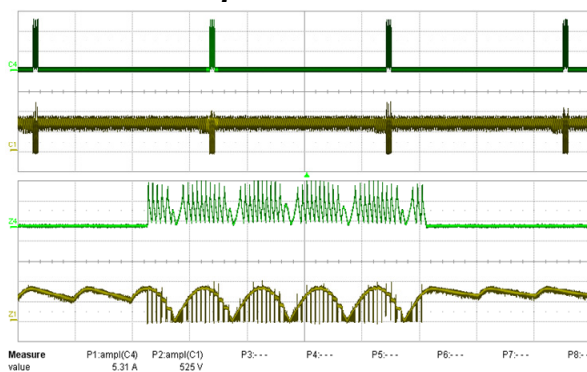


Figure 24 – 265 VAC, Full Load.
Upper: I_{OUT} , 2 A / div.
Lower: V_{DRAIN} , 200 V, 500 ms / div.

12.7 Output Current and Output Voltage with Shorted Output

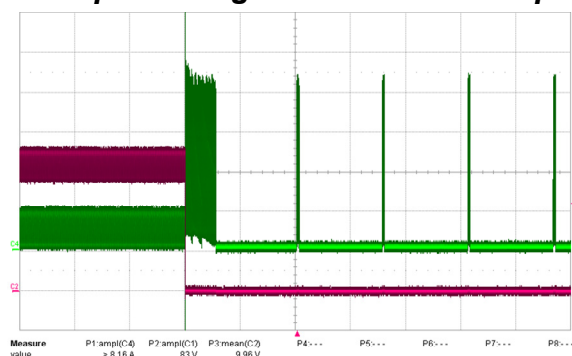


Figure 25 – 110 VAC, Full Load.
Upper: I_{OUT} , 1 A / div.
Lower: V_{DRAIN} , 10 V, 1 s / div.

12.8 Open Load Output Voltage

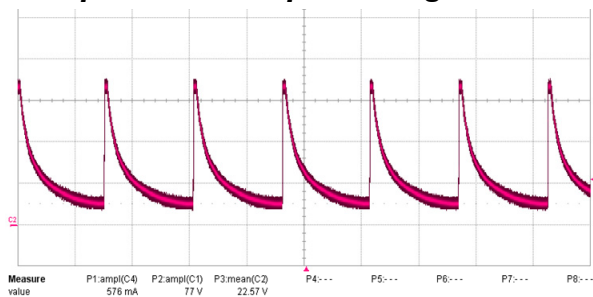


Figure 26 – Output Voltage: 110 VAC.
 V_{OUT} , 20 V / div., 1 s / div.

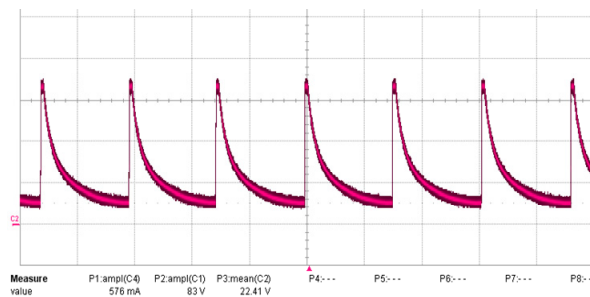


Figure 27 – Output Voltage: 230 VAC.
 V_{OUT} , 20 V / div., 1 s / div.

Note: Under open load conditions the OV shutdown function is designed to prevent the output voltage exceeding SELV limits (45 V). This is achieved, however the voltage rating of the output capacitors is exceeded which is acceptable for a fault condition.

13 Line Surge

Differential and common input line 200 A ring wave testing was completed on a single test unit to IEC61000-4-5. Input voltage was set at 230 VAC / 60 Hz. Output was loaded at full load and operation was verified following each surge event.

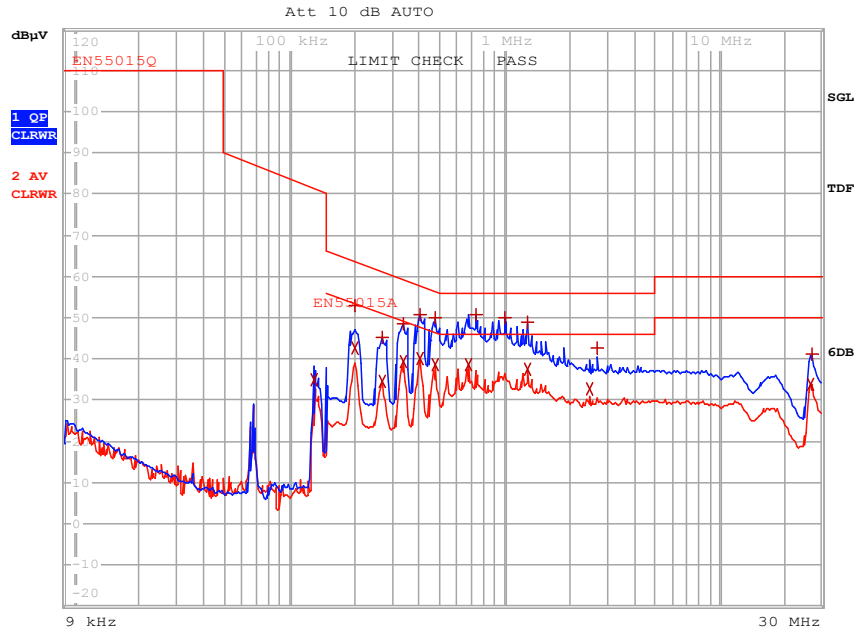
Surge Level (V)	Input Voltage (VAC)	Injection Location	Injection Phase (°)	Test Result (Pass/Fail)
2500	230	L to N	90	Pass
2500	230	L to N	90	Pass
2500	230	L to PE	90	Pass
2500	230	L to PE	90	Pass
2500	230	N to PE	90	Pass
2500	230	N to PE	90	Pass

Unit passes under all test conditions.



14 Conducted EMI

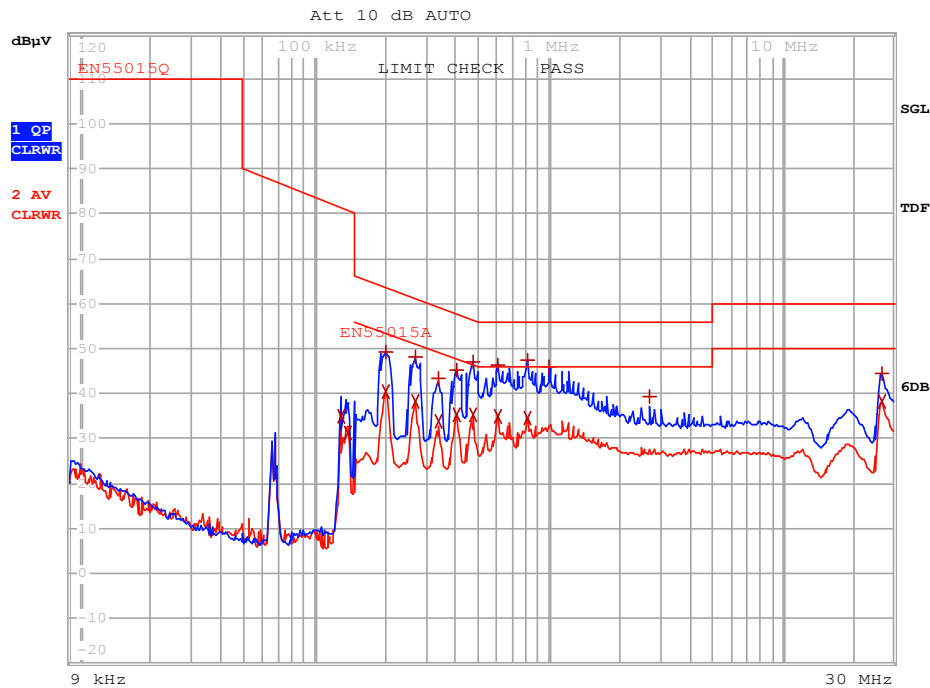
Note: Refer to table for margin to standard – blue line is peak measurement but limit line is quasi peak.



EDIT PEAK LIST (Final Measurement Results)						
Trace1:	EN55015Q					
Trace2:	EN55015A					
Trace3:	---					
TRACE	FREQUENCY	LEVEL dBμV	DELTA	LIMIT	dB	
2 Average	129.530094744 kHz	35.95	L1	gnd		
1 Quasi Peak	200.175581485 kHz	52.81	N	gnd	-10.79	
2 Average	202.1773373 kHz	42.64	N	gnd	-10.87	
1 Quasi Peak	269.806440381 kHz	45.18	L1	gnd	-15.93	
2 Average	269.806440381 kHz	34.74	L1	gnd	-16.38	
1 Quasi Peak	335.832355405 kHz	48.52	L1	gnd	-10.78	
2 Average	335.832355405 kHz	39.33	L1	gnd	-9.97	
1 Quasi Peak	401.705024172 kHz	50.78	L1	gnd	-7.03	
2 Average	401.705024172 kHz	39.84	L1	gnd	-7.97	
1 Quasi Peak	471.030732902 kHz	49.88	N	gnd	-6.61	
2 Average	471.030732902 kHz	38.39	N	gnd	-8.09	
1 Quasi Peak	673.936068749 kHz	50.60	L1	gnd	-5.39	
2 Average	673.936068749 kHz	38.39	L1	gnd	-7.60	
1 Quasi Peak	1.00339897152 MHz	49.91	L1	gnd	-6.08	
2 Average	1.27405044044 MHz	48.88	N	gnd	-7.11	
2 Average	1.27405044044 MHz	37.38	N	gnd	-8.61	
2 Average	2.48152506244 MHz	32.47	N	gnd	-13.52	
1 Quasi Peak	2.68713605405 MHz	42.58	N	gnd	-13.41	
1 Quasi Peak	26.4975442467 MHz	40.33	L1	gnd	-19.67	
2 Average	26.4975442467 MHz	33.40	L1	gnd	-16.59	

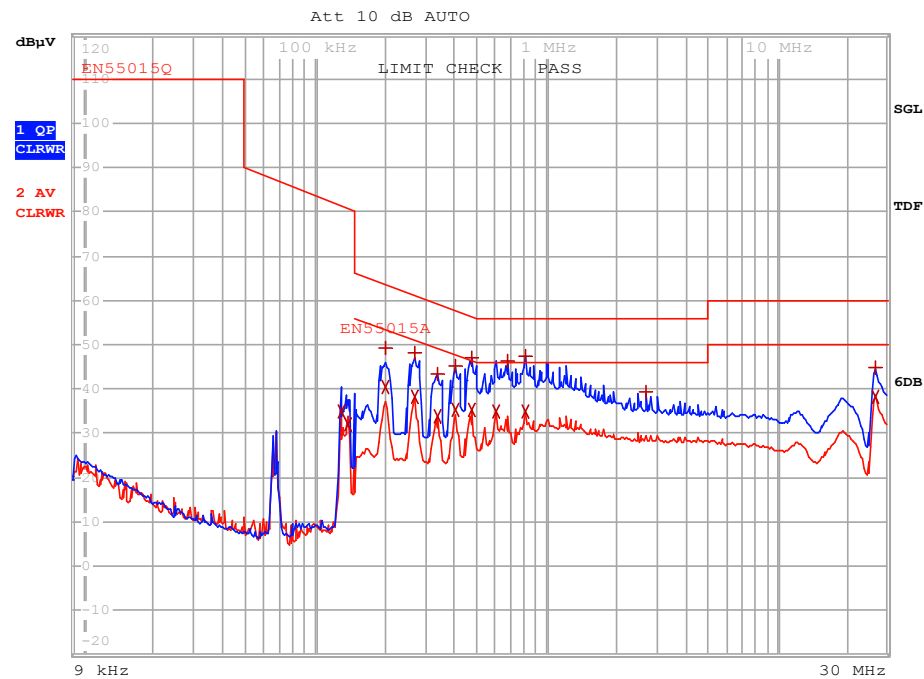
Figure 28 – Conducted EMI, Maximum Steady-State Load, 230 VAC, Line, 60 Hz, and EN55015 B Limits.





EDIT PEAK LIST (Final Measurement Results)						
Trace1:	EN55015Q					
Trace2:	EN55015A					
Trace3:	---					
TRACE	FREQUENCY	LEVEL dBμV	DELTA	LIMIT	dB	
2 Average	129.530094744 kHz	34.89	N	gnd		
2 Average	138.873793737 kHz	31.26	N	gnd		
1 Quasi Peak	202.1773373 kHz	49.31	L1	gnd	-14.20	
2 Average	202.1773373 kHz	40.53	L1	gnd	-12.99	
1 Quasi Peak	269.806440381 kHz	48.00	L1	gnd	-13.12	
2 Average	269.806440381 kHz	38.13	L1	gnd	-12.98	
1 Quasi Peak	335.832355405 kHz	43.28	N	gnd	-16.02	
2 Average	335.832355405 kHz	33.71	N	gnd	-15.58	
1 Quasi Peak	401.705024172 kHz	45.29	L1	gnd	-12.52	
2 Average	401.705024172 kHz	35.13	L1	gnd	-12.68	
1 Quasi Peak	471.030732902 kHz	47.20	N	gnd	-9.28	
2 Average	471.030732902 kHz	35.35	N	gnd	-11.13	
1 Quasi Peak	604.06488251 kHz	46.47	L1	gnd	-9.52	
2 Average	604.06488251 kHz	34.78	L1	gnd	-11.21	
1 Quasi Peak	806.126927408 kHz	47.44	L1	gnd	-8.55	
2 Average	806.126927408 kHz	34.72	L1	gnd	-11.28	
1 Quasi Peak	1.00339897152 MHz	46.12	L1	gnd	-9.87	
1 Quasi Peak	2.68713605405 MHz	39.24	N	gnd	-16.75	
1 Quasi Peak	26.4975442467 MHz	44.55	N	gnd	-15.44	
2 Average	26.4975442467 MHz	38.30	L1	gnd	-11.69	

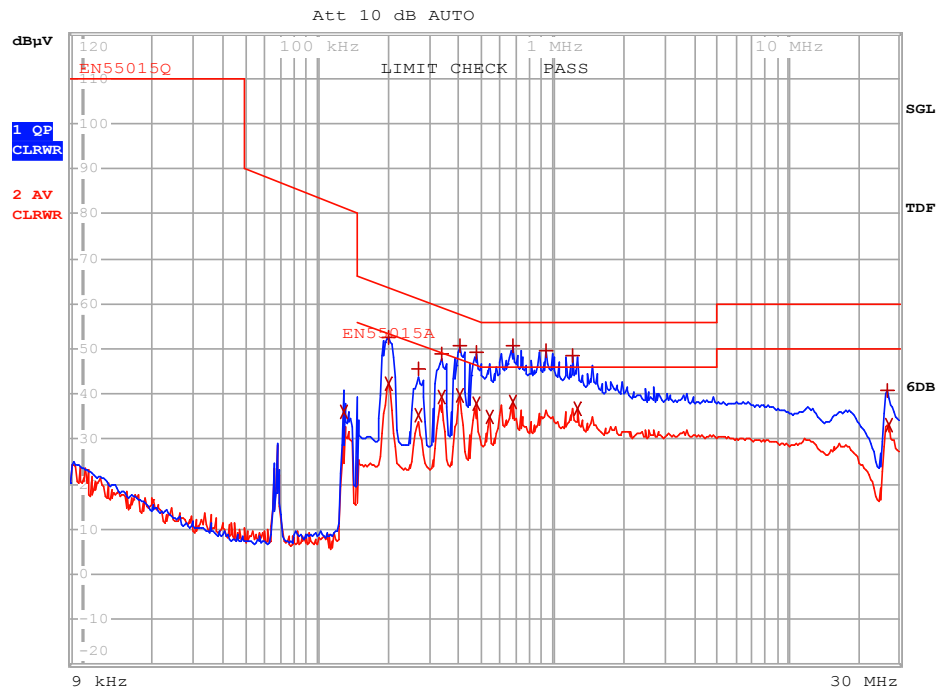
Figure 29 – Conducted EMI, Maximum Steady-State Load, 110 VAC, Line, 60 Hz, and EN55015 B Limits.



EDIT PEAK LIST (Final Measurement Results)						
Trace1:	EN55015Q					
Trace2:	EN55015A					
Trace3:	---					
TRACE	FREQUENCY	LEVEL dBμV	DELTA	LIMIT	dB	
2 Average	129.530094744 kHz	35.08	N	gnd		
2 Average	138.873793737 kHz	32.16	N	gnd		
1 Quasi Peak	202.1773373 kHz	49.32	L1	gnd	-14.19	
2 Average	202.1773373 kHz	40.56	L1	gnd	-12.96	
1 Quasi Peak	269.806440381 kHz	48.00	L1	gnd	-13.12	
2 Average	269.806440381 kHz	38.19	L1	gnd	-12.92	
1 Quasi Peak	335.832355405 kHz	43.26	N	gnd	-16.04	
2 Average	335.832355405 kHz	33.71	N	gnd	-15.58	
1 Quasi Peak	401.705024172 kHz	45.34	L1	gnd	-12.47	
2 Average	401.705024172 kHz	35.24	L1	gnd	-12.57	
1 Quasi Peak	471.030732902 kHz	47.17	N	gnd	-9.32	
2 Average	471.030732902 kHz	35.36	N	gnd	-11.13	
2 Average	604.06488251 kHz	34.86	L1	gnd	-11.13	
1 Quasi Peak	673.936068749 kHz	46.31	N	gnd	-9.68	
1 Quasi Peak	806.126927408 kHz	47.47	L1	gnd	-8.52	
2 Average	806.126927408 kHz	34.78	L1	gnd	-11.21	
1 Quasi Peak	2.68713605405 MHz	39.33	N	gnd	-16.67	
1 Quasi Peak	26.4975442467 MHz	44.69	L1	gnd	-15.30	
2 Average	26.4975442467 MHz	38.39	L1	gnd	-11.60	

Figure 30 – Conducted EMI, Maximum Steady-State Load, 110 VAC, Neutral, 60 Hz, and EN55015 B Limits.





EDIT PEAK LIST (Final Measurement Results)					
Trace1:	EN55015Q				
Trace2:	EN55015A				
Trace3:	---				
TRACE	FREQUENCY	LEVEL dBµV	DELTA	LIMIT	dB
2 Average	129.530094744 kHz	35.87	N gnd		
1 Quasi Peak	202.1773373 kHz	52.66	N gnd	-10.85	
2 Average	202.1773373 kHz	42.36	N gnd	-11.15	
1 Quasi Peak	269.806440381 kHz	45.66	L1 gnd	-15.45	
2 Average	269.806440381 kHz	35.44	L1 gnd	-15.68	
1 Quasi Peak	335.832355405 kHz	48.74	L1 gnd	-10.56	
2 Average	335.832355405 kHz	39.49	L1 gnd	-9.81	
1 Quasi Peak	401.705024172 kHz	50.62	L1 gnd	-7.18	
2 Average	401.705024172 kHz	39.57	N gnd	-8.24	
1 Quasi Peak	471.030732902 kHz	49.08	N gnd	-7.40	
2 Average	471.030732902 kHz	37.96	N gnd	-8.53	
2 Average	536.076911993 kHz	34.96	N gnd	-11.03	
1 Quasi Peak	673.936068749 kHz	50.80	L1 gnd	-5.19	
2 Average	673.936068749 kHz	38.39	L1 gnd	-7.61	
1 Quasi Peak	945.247220176 kHz	49.46	L1 gnd	-6.53	
1 Quasi Peak	1.21221527836 MHz	48.43	N gnd	-7.57	
2 Average	1.27405044044 MHz	36.86	N gnd	-9.13	
1 Quasi Peak	26.4975442467 MHz	40.99	L1 gnd	-19.00	
2 Average	26.7625196891 MHz	33.19	L1 gnd	-16.80	

Figure 31 – Conducted EMI, Maximum Steady-State Load, 230 VAC, Neutral, 60 Hz, and EN55015 B Limits.

15 Revision History

Date	Author	Revision	Description and Changes	Reviewed
18-Jul-11	ME	1.0	Initial Release	Apps and Mktg



For the latest updates, visit our website: www.powerint.com

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